

YJ Planar Schottky Barrier Diode Die Specification

60V 20A, 120mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB120M060SS-280A

Main Products Characterstics

Maximum Ratings

Symbol	Unit	Value
I_F	A	20
V_{RRM}	V	60
T_J	°C	175
T_{stg}	°C	250
t_{JW}	s	10
t_{JH}	s	10
t_{JL}	s	10
t_{JH}	s	10
t_{JL}	s	10

Static Electrical Characteristics (Ta = 25°C)

Symbol	Unit	Value
I_F	A	20
V_{RRM}	V	60
T_J	°C	175
T_{stg}	°C	250
t_{JW}	s	10
t_{JH}	s	10
t_{JL}	s	10
t_{JH}	s	10
t_{JL}	s	10

Device Schematics and Outline Drawing

Symbol	Unit	Value
I_F	A	20
V_{RRM}	V	60
T_J	°C	175
T_{stg}	°C	250
t_{JW}	s	10
t_{JH}	s	10
t_{JL}	s	10
t_{JH}	s	10
t_{JL}	s	10

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal